

Nch 800V 2A Power MOSFET

V_{DSS}	800V
R _{DS(on)} (Max.)	4.3Ω
I _D	2A
P_D	36W

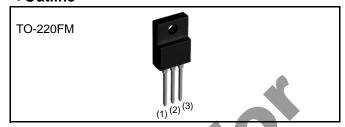
● Features

- 1) Low on-resistance.
- 2) Fast switching speed.
- 3) Gate-source voltage (V_{GSS}) guaranteed to be $\pm 30V$.
- 4) Drive circuits can be simple.
- 5) Parallel use is easy.
- 6) Pb-free lead plating; RoHS compliant

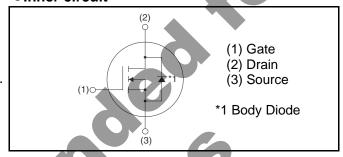
Application

Switching Power Supply

Outline



●Inner circuit



Packaging specifications

Tackaging specifications				
	Packaging	Bulk		
	Reel size (mm)	-		
Type	Tape width (mm)	-		
Туре	Basic ordering unit (pcs)	500		
	Taping code	-		
	Marking	R8002ANX		

• Absolute maximum ratings $(T_a = 25^{\circ}C)$

Parameter	Symbol	Value	Unit
Drain - Source voltage	V_{DSS}	800	V
Continuous drain current	I _D *1	±2	А
T _c = 100° C	l _D *1	±1	А
Pulsed drain current	l _{D,pulse} *2	±8	А
Gate - Source voltage	V_{GSS}	±30	V
Avalanche energy, single pulse	E _{AS} *3	0.265	mJ
Avalanche energy, repetitive	E _{AR} *4	0.212	mJ
Avalanche current	I _{AR} *3	1	А
Power dissipation (T _c = 25°C)	P _D	36	W
Junction temperature	T _j	150	°C
Range of storage temperature	T_{stg}	-55 to +150	°C
Reverse diode dv/dt	dv/dt *5	15	V/ns

Absolute maximum ratings

Parameter	Symbol	Conditions	Values	Unit
Drain - Source voltage slope	dv/dt	$V_{DS} = 480V, I_{D} = 2A$ $T_{j} = 125^{\circ}C$	50	V/ns

●Thermal resistance

Parameter	Symbol	Values			Unit
- Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R_{thJC}	-		3.41	°C/W
Thermal resistance, junction - ambient	R_{thJA})'	70	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}		-	265	°C

•Electrical characteristics($T_a = 25$ °C)

Soldering temperature, wavesoldering for 10s			T _{sold}	-	-	265	°C
●Electrical characteristics(T _a = 25°C)							
Parameter	Symbol	Co	onditions	V	Values		Unit
				Min.	Тур.	Max.	
Drain - Source breakdown voltage	V _{(BR)DSS}	$V_{GS} = 0V$	$I_{\rm r}$ $I_{\rm D}$ = 1mA	800	1	-	V
Drain - Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS} = 0V$	$I_D = 2A$	-	900	-	V
Zero gate voltage drain current	I _{DSS}	$V_{DS} = 80$ $T_{j} = 25^{\circ}C$ $T_{j} = 125^{\circ}$			0.1	100 1000	μΑ
Gate - Source leakage current	I _{GSS}	$V_{GS} = \pm 3$	$0V, V_{DS} = 0V$	-	-	±100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = 10^{\circ}$	$V, I_D = 1mA$	3	-	5	V
		$V_{GS} = 10$	V, I _D = 1A				
Static drain - source on - state resistance	R _{DS(on)} *6	T _j = 25°C	;	_	3.3	4.3	Ω
		T _j = 125°	С	_	6.63	-	
Gate input resistance	R_{G}	f = 1MHz	z, open drain	-	5.9	-	Ω

●Electrical characteristics(T_a = 25°C)

Parameter	Symbol	Conditions	Conditions			Unit
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Transconductance	g _{fs} *6	$V_{DS} = 10V, I_{D} = 1.0A$	0.5	1	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	210	-	
Output capacitance	C _{oss}	V _{DS} = 25V	-	130		pF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	14		
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$,	-	15.5	-	
Effective output capacitance, time related	C _{o(tr)}	$V_{DS} = 0V \text{ to } 480V$	C	15.6	-	pF
Turn - on delay time	t _{d(on)} *6	$V_{DD} \simeq 400V$, $V_{GS} = 10V$	<u>J.</u>	17	-	
Rise time	t _r *6	I _D = 1A	-	20	-	20
Turn - off delay time	t _{d(off)} *6	$R_L = 400\Omega$		33	66	ns
Fall time	t _f *6	$R_G = 10\Omega$		70	140	

●Gate Charge characteristics(T_a = 25°C)

Parameter	Symbol Conditions -		Values			Unit
raiailletei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	Q_g^{*6}	V _{DD} ≃ 400V	-	12.7	ı	
Gate - Source charge	Q _{gs} *6	$I_D = 2A$	-	2.7	-	nC
Gate - Drain charge	Q _{gd} *6	V _{GS} = 10V	-	4.3	-	
Gate plateau voltage	V _(plateau)	$V_{DD} \simeq 400V$, $I_D = 2A$	-	7.4	-	V

^{*1} Limited only by maximum temperature allowed.

^{*2} Pw \leq 10 μ s, Duty cycle \leq 1%

^{*3} L $^{\simeq}$ 500 μ H, V_{DD} = 50V, R_{G} = 25 Ω , starting T_{j} = 25°C

^{*4} L $^{\sim}$ 500 μ H, V_{DD} = 50V, R_G = 25 Ω , starting T_j = 25°C, f = 10kHz

^{*5} Reference measurement circuits Fig.5-1.

^{*6} Pulsed

●Body diode electrical characteristics (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
r ai ai i letei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Inverse diode continuous, forward current	l _S *1	T _c = 25°C	-	,	2	A
Inverse diode direct current, pulsed	I _{SM} *2	11 _c = 25 G	'	-	8	A
Forward voltage	V _{SD} *6	$V_{GS} = 0V, I_S = 2A$	-	-	1.5	V
Reverse recovery time	t _{rr} *6		-	481	-	ns
Reverse recovery charge	Q _{rr} *6	I _S = 2A di/dt = 100A/us		2.5	-	μС
Peak reverse recovery current	I _{rrm} *6]	10.5	-	Α
Peak rate of fall of reverse recovery current	di _{rr} /dt	T _j = 25°C	-	50	-	A/μs

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	0.486	
R _{th2}	1.31	K/W
R _{th3}	1.96	

Symbol	Value	Unit
C _{th1}	0.00095	
C _{th2}	0.0112	Ws/K
C_{th3}	0.521	

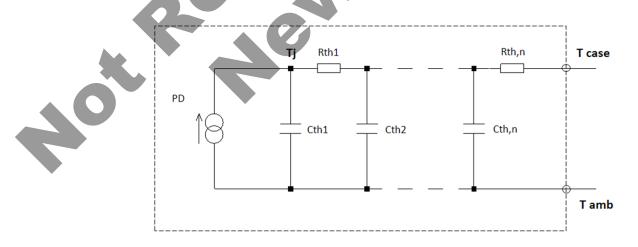
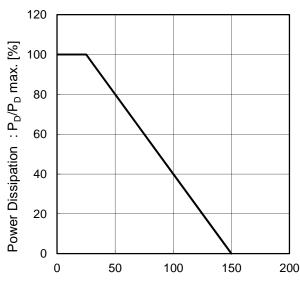
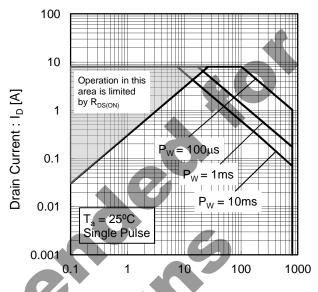


Fig.1 Power Dissipation Derating Curve



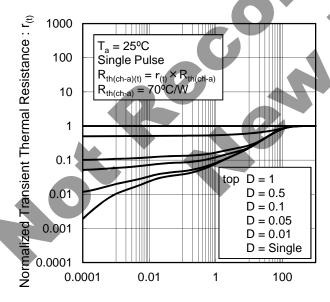
Junction Temperature : Tj [°C]

Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]

Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



Pulse Width : P_W [s]

Fig.4 Avalanche Current vs Inductive Load

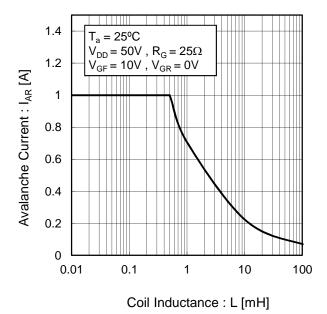
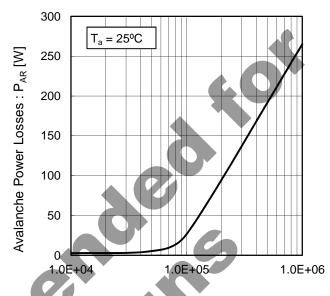
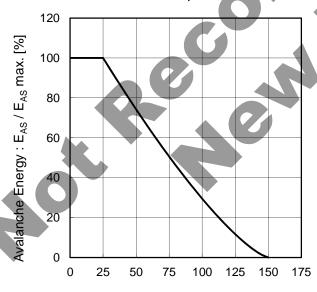


Fig.5 Avalanche Power Losses



Frequency: f [Hz]

Fig.6 Avalanche Energy Derating Curve vs Junction Temperature



Junction Temperature : T_i [°C]

Fig.7 Typical Output Characteristics(I)

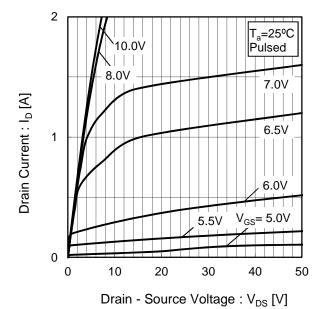


Fig.8 Typical Output Characteristics(II)

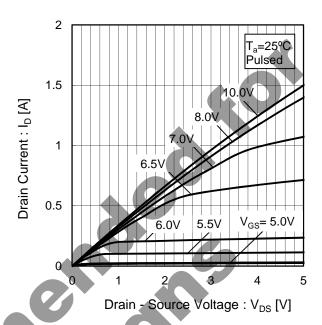
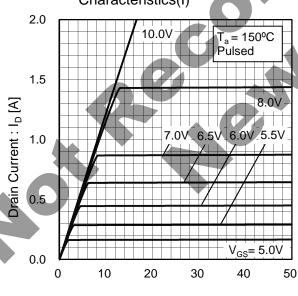
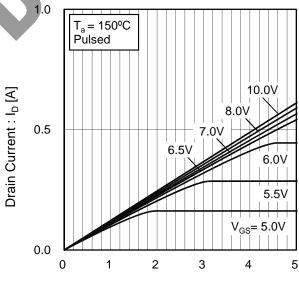


Fig.9 T_j = 150°C Typical Output Characteristics(I)

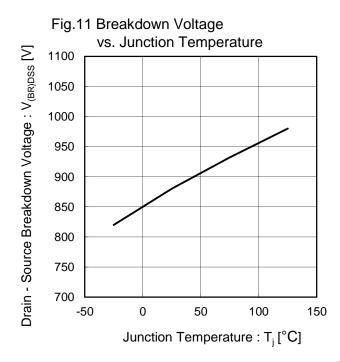


Drain - Source Voltage : V_{DS} [V]

Fig.10 $T_j = 150$ °C Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]



10 $V_{DS} = 10V$ Pulsed 1 $T_a = 125^{\circ}C$ $T_a = 75^{\circ}C$ $T_a = 25^{\circ}C$ $T_a = -25^{\circ}C$ $T_a = -25^{\circ}$

Fig.12 Typical Transfer Characteristics

Fig. 13 Gate Threshold Voltage
vs. Junction Temperature

VDS=10V
VDS=1

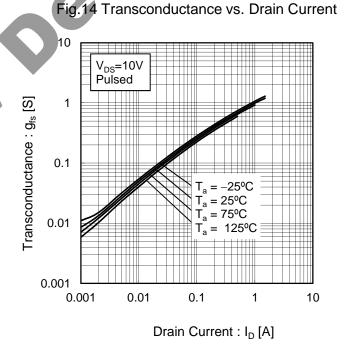


Fig.15 Static Drain - Source On - State Resistance vs. Gate Source Voltage

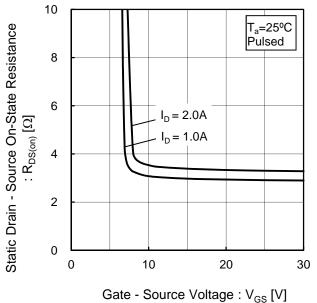
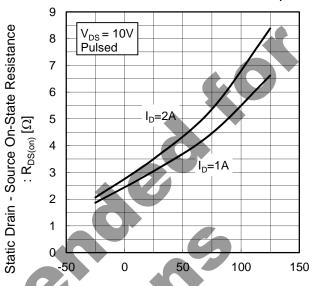
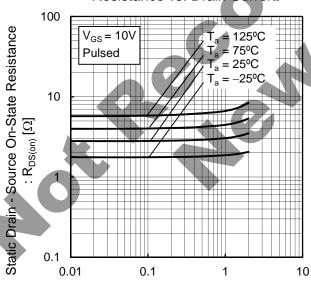


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature



Junction Temperature : T_i [°C]

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current



Drain Current : I_D [A]

Fig.18 Typical Capacitance vs. Drain - Source Voltage 10000 T_a=25°C f=1MHz V_{GS}=0V 1000 Capacitance: C [pF] C_{iss} 100 10 $\mathsf{C}_{\mathsf{rss}}$ 0.01 0.1 10 100 1000 Drain - Source Voltage : $V_{DS}[V]$

T_a = 25°C

Fig.19 Coss Stored Energy

Fig.20 Switching Characteristics

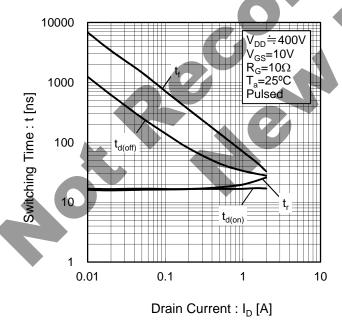


Fig.21 Dynamic Input Characteristics

Drain - Source Voltage : V_{DS} [V]

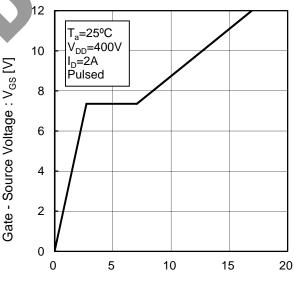


Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

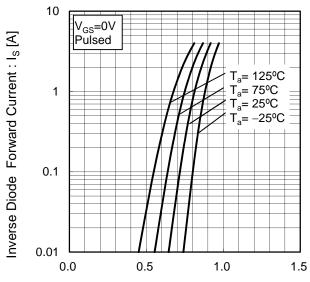
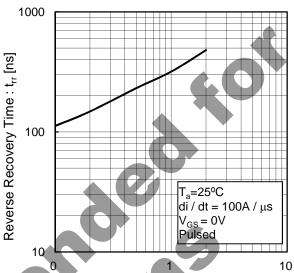


Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Inverse Diode Forward Current : I_S [A]



Source - Drain Voltage : V_{SD} [V]

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Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

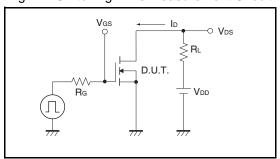


Fig.2-1 Gate Charge Measurement Circuit

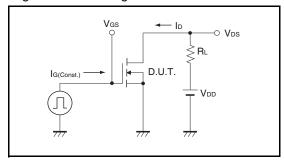


Fig.3-1 Avalanche Measurement Circuit

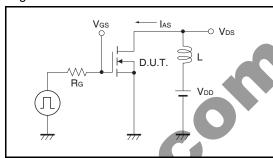


Fig.4-1 dv/dt Measurement Circuit

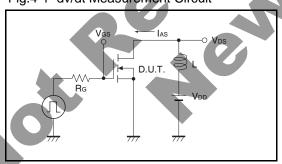


Fig.5-1 di/dt Measurement Circuit

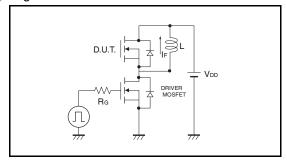


Fig.1-2 Switching Waveforms

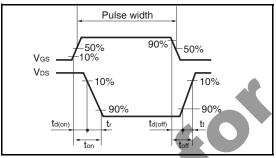


Fig.2-2 Gate Charge Waveform

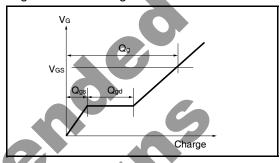


Fig.3-2 Avalanche Waveform

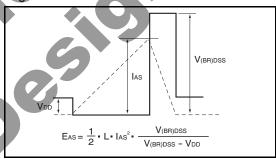


Fig.4-2 dv/dt Waveform

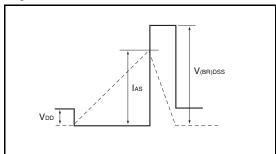
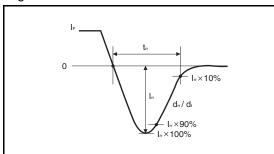
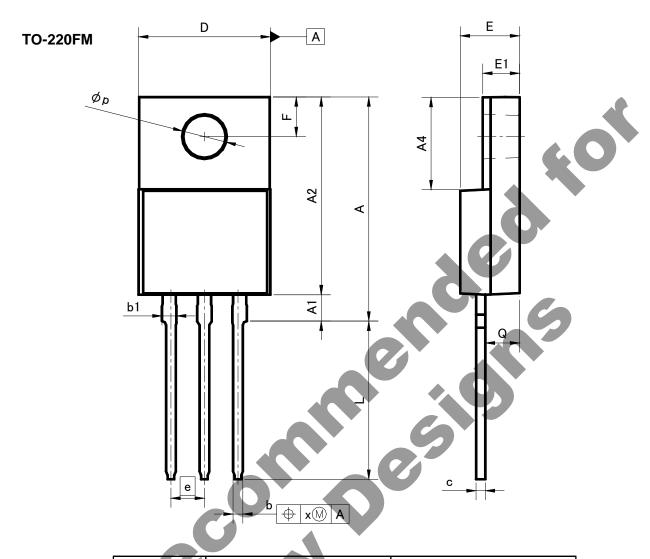


Fig.5-2 di/dt Waveform



●Dimensions (Unit : mm)



DIM	MILIM	MILIMETERS		HES
DIW	MIN	MAX	MIN	MAX
A	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
С	0.70	0.85	0.028	0.033
D	9.90	10.30	0.39	0.406
Е	4.40	4.80	0.173	0.189
е	2.54		0.	10
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.11	0.126
L	11.50	12.50	0.453	0.492
р	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
Х	_	0.381	_	0.015

Dimension in mm/inches

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 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (even if you use no-clean type fluxes, cleaning residue of flux is recommended); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
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- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse. is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power, exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
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 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- 2. Even under ROHM recommended storage condition, solderability of products out of recommended storage time period may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is exceeding the recommended storage time period.
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